AT01

Ferromagnetic Phase in Bulk (Cd,Cr) Te Dilute Magnetic Semiconductor

Kowan-Young Ko* School of Mechanical Engineering, Ulsan College University, Ulsan Metropolitan City, 680-749, S. Korea *Corresponding author: K. Y. Ko, e-mail: kyko@mail.uc.ac.kr

Ferromagnetic behaviors in dilute magnetic semiconductor at room temperature remain still elusive [1]. Ko and Blamire [2] reported that ferromagnetism with a Curie temperature \sim 395 K in Cr-doped CdTe dilute magnetic semiconductor could be explained by ferromagnetic interaction between Cr atoms dissolved in the CdTe matrix. Recently Stefaniuk et al. [3] analyzed ferromagnetic resonance in sintered Cd1-xCrxTe solid solution at room temperature through Kittle and Van Vleck theories. Room temperature ferromagnetic phase in bulk Cr-doped CdTe crystal are reported using X-ray diffraction, field emission transmission electron microscopy (FE-TEM), EDX and SQUID. Electron diffraction and lattice image in Fig. 1 showed that it completely correspond with single-phased zincblende structure. It displayed with no existence of second phase such as NiAs-CrTe, MnP-CrTe, Cr₂Te₃ and Cr₃Te₄ compounds. Magnetic measurements in a temperature range of $5 \sim 500$ K under zero field cooling (ZFC) and field cooling (FC) showed temperature induced



Fig. 1. TEM micrographs and temperature dependent magnetization curves.

ferro-magnetic phase shift of ~ 20 K with a Curie temperature ~ 362 K. Ferro-magnetic phase (H_c ≈ 100 Oe) with ~ 0.025 μ_B per Cr-atom is unlikely to be associated with impurity phases, and is coupling between Cr atoms dissolved in the CdTe matrix. The deviation between ZFC and FC seem to be similar with spin glass-like V-doped ZnO film [4].

This work was supported by the 2007 Research Fund of the Ulsan College University.

REFERENCES

[1] X. Y. Cui, D. Ferandez-Hevia, B. Delley, A. J. Freeman and C. Stampfl, J. Appl. Phys. 101, 103917(2007).

- [2] K. Y. Ko and M. G. Blamire, Appl. Phys. Lett. 88, 172101(2006).
- [3] I. Stefaniuk, M. Bester and M. Kuzma, J. Phys. **104**, 012010(2008).
- [4] N. H. Hong, J. Sakai and A. Hassini, J. Phys. Condens. Matter 17, 199(2005).

AT02

Magnetic and Structural Studies on Fe Doped ZnO thin Films Deposited by RF Magnetron Sputtering

Soo-Young Seo, Chang-Ha Kwak, and Seon-Hyo Kim*

Pohang University of Science and Technology, San 31, Hyoja-dong Pohang, Kyungbuk, 790-784, Korea *Corresponding author: Author1 kim, e-mail: sconhyo@postech.ac.kr

Abstract

A high quality Fe doped ZnO thin films were fabricated on a α -sapphire substrate by RF magnetron sputtering. We present the magnetic and structural properties of Zn_{1-x}Fe_xO films with various thickness. The structures of Zn_{1-x}Fe_xO thin films with the composition ratio of Fe were studied with FE-SEM, XRD, AFM and x-ray absorption fine structure measurements. The XRD measurements showed that Zn_{1-x}Fe_xO films have a wurtzite structure like ZnO crystals. However, the (0002) diffraction peak moved from $2\theta = 34.42^{\circ}$ to 34.1° as x is increased. This implied that the lattice constant c was increased by about 0.047 Å due to Fe replacement on the Zn site in the Zn_{1-x}Fe_xO films. The structural environments around Zn atoms in Zn_{1-x}Fe_xO thin films were studied with XAFS. XPS measurements were employed to characterize the valence state of Fe ions. In the XPS measurements revealed the evidence for the coexistence of the Fe³⁺ and Fe²⁺ ions. And by the XPS data, we can rule out the existence of Fe metal clusters. In addition, we introduce Superconducting Quantum Interference Device measurement (SQUID) in order to determine the magnetic properties of Zn_{1-x}Fe_xO.



Fig. 1. M-H curve of Zn_{0.95}Fe_{0.05}O films grown on a α-sapphire substrates measured at 5K.

Keywords : rf-magnetron sputtering, ZnO, XPS, XAFS, magnetic property.